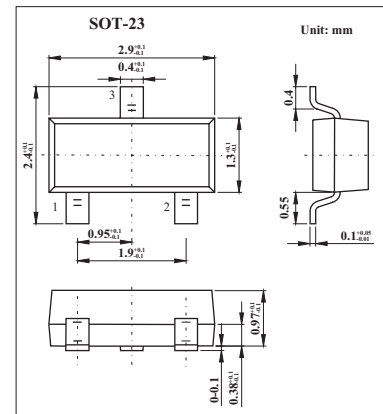


## Schottky Barrier Diode

## MMBD301



### ■ Features

### ■ Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Working Inverse Voltage	$W_{IV}$	25	V
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$	pF	200	mW
Derate above $25^\circ\text{C}$		2.0	mW/ $^\circ\text{C}$
Storage temperature range	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +125	$^\circ\text{C}$

### ■ Electrical Characteristics $T_A = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown Voltage	BV	$I_R = 10 \mu\text{A}$	30		V
Reverse Leakage	$I_R$	$V_R = 25\text{V}$		200	nA
Forward Voltage	$V_F$	$I_F = 1.0\text{mA}$		450	mV
		$I_F = 10\text{mA}$		600	
Capacitance	$C_T$	$V_R = 15\text{V}, f = 1.0\text{MHz}$		1.5	pF

### ■ Marking

Marking	4T
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